

Radiation Hardened EDAC (Error Detection and Correction Circuit)

January 1996

Features

- Devices QML Qualified in Accordance with MIL-PRF-38535
- Detailed Electrical and Screening Requirements are Contained in SMD# 5962-96711 and Intersil' QM Plan
- 1.25 Micron Radiation Hardened SOS CMOS
- Total Dose>300K RAD (Si)
- Single Event Upset (SEU) Immunity: <1 x 10⁻¹⁰ Errors/Bit/Day (Typ)
- SEU LET Threshold>100 MEV-cm²/mg
- Dose Rate Upset>10¹¹ RAD (Si)/s, 20ns Pulse
- Dose Rate Survivability.....>10¹² RAD (Si)/s, 20ns Pulse
- Latch-Up Free Under Any Conditions
- Military Temperature Range -55°C to +125°C
- Significant Power Reduction Compared to ALSTTL Logic
- DC Operating Voltage Range 4.5V to 5.5V
- Input Logic Levels
 - VIL = 30% of VCC Max
 - VIH = 70% of VCC Min
- Input Current ≤ 1µA at VOL, VOH

Description

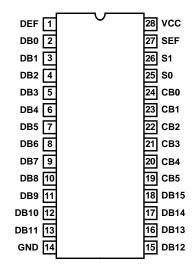
The Intersil ACS630MS is a Radiation Hardened 16-bit parallel error detection and correction circuit. It uses a modified Hamming code to generate a 6-bit check word from each 16-bit data word. The check word is stored with the data word during a memory write cycle; during a memory read cycle a 22-bit word is taken form memory and checked for errors. Single bit errors in the data words are flagged and corrected. Single bit errors in check words are flagged but not corrected. The position of the incorrect bit is pinpointed, in both cases, by the 6-bit error syndrome code which is output during the error correction cycle.

The ACS630MS utilizes advanced CMOS/SOS technology to achieve high-speed operation. This device is a member of a radiation hardened, high-speed, CMOS/SOS Logic Family.

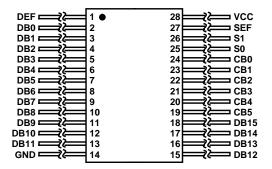
The ACS630MS is supplied in a 28 lead Ceramic Flatpack (K suffix) or a 28 Lead Ceramic Dual-In-Line Package (D suffix).

Pinouts

28 PIN CERAMIC DUAL-IN-LINE, MIL-STD-1835 DESIGNATOR CDIP2-T28, LEAD FINISH C TOP VIEW



28 PIN CERAMIC FLATPACK, MIL-STD-1835 DESIGNATOR CDFP3-F28, LEAD FINISH C TOP VIEW



Ordering Information

PART NUMBER	TEMPERATURE RANGE	SCREENING LEVEL	PACKAGE
5962F9671101VXC	-55°C to +125°C	MIL-PRF-38535 Class V	28 Lead SBDIP
5962F9671101VYC	-55°C to +125°C	MIL-PRF-38535 Class V	28 Lead Ceramic Flatpack
ACS630D/Sample	25°C	Sample	28 Lead SBDIP
ACS630K/Sample	25°C	Sample	28 Lead Ceramic Flatpack
ACS630HMSR	25°C	Die	Die

Function Tables

Control Functions

MEMORY CONTROL						ERROR FLAGS			
CYCLE	S1	S0	EDAC FUNCTION	DATA I/O	CHECKWORD	SEF	DEF		
WRITE	Low	Low	Generates Checkword	Input Data	Output Checkword	Low	Low		
READ	Low	High	Read Data and Check- word	Input Data	Input Checkword	Low	Low		
READ	High	High	Latch and Flag Error	Latch Data	Latch Checkword	Enabled	Enabled		
READ	High	Low	Correct Data Word and Generate Syndrome Bits	Output Corrected Data	Output Syndrome Bits	Enabled	Enabled		

Check Word Generation

		16-BIT DATA WORD														
CHECKWORD BIT	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15
CB0	Х	Х		Х	Х				Х	Х	Х			Х		
CB1	Х		Х	Х		Х	Х		Х			Х			Х	
CB2		Х	Х		Х	Х		Х		Х			Х			Х
CB3	Х	Х	Х				Х	Х			Х	Х	Х			
CB4				Х	Х	Х	Х	Х						Х	Х	Х
CB5									Х	Х	Х	Х	Х	Х	Х	Х

NOTE: The six check bits are parity bits derived from the matrix of data bits as indicated by "x" for each bit

Error Syndrome Codes

		ERROR LOCATIONS																					
SYNDROME								D	В								СВ						NO
CODE	0	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	0	1	2	3	4	5	ERROR
CB0	L	L	Н	L	L	Н	Н	Н	L	L	L	Н	Н	L	Н	Н	L	Н	Н	Н	Н	Н	Н
CB1	L	Н	L	L	Н	L	L	Н	L	Н	Н	L	Н	Н	L	Н	Н	L	Н	Н	Н	Н	Н
CB2	Н	L	L	Н	L	L	Н	L	Н	L	Н	Н	L	Н	Н	L	Н	Н	L	Н	Н	Н	Н
CB3	L	L	L	Н	Н	Н	L	L	Н	Н	L	L	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н
CB4	Η	Н	Н	L	L	L	L	L	Н	Н	Н	Н	Н	L	L	L	Η	Н	Н	Н	L	Н	Н
CB5	Ι	Η	Η	Η	Η	Η	Η	Н	L	L	L	L	L	L	L	L	Ι	Η	Н	Н	Η	L	Н

Error Functions

TOTAL NUMB	ER OF ERRORS	ERROR		
16-BIT DATA	6-BIT CHECKWORD	SEF	DEF	DATA CORRECTION
0	0	Low	Low	Not Applicable
1	0	High	Low	Correction
0	1	High	Low	Correction
1	1	High	High	Interrupt
2	0	High	High	Interrupt
0	2	High	High	Interrupt

Die Characteristics

DIE DIMENSIONS:

171 mils x 159 mils 4340mm x 4040mm

METALLIZATION:

Type: AISi

Metal 1 Thickness: 7.125kÅ ±1.125kÅ

Metal 2 Thickness: 9kÅ ±1kÅ

GLASSIVATION:

Type: SiO₂

Thickness: 8kÅ ±1kÅ

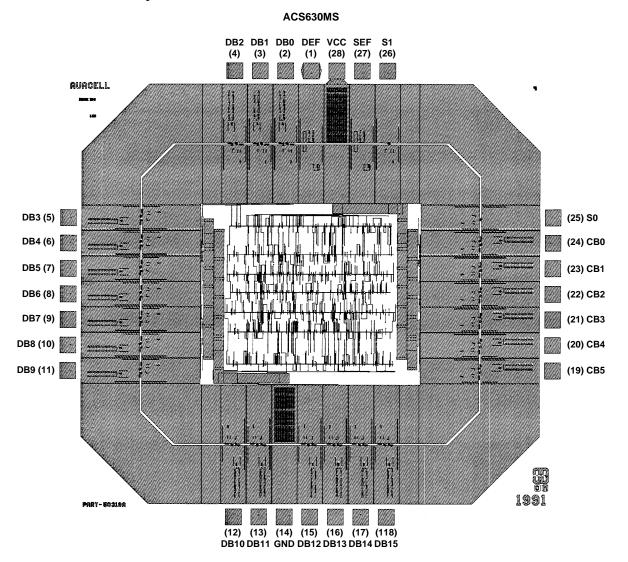
WORST CASE CURRENT DENSITY:

 $< 2.0 \times 10^5 \text{A/cm}^2$

BOND PAD SIZE:

110μm x 110μm 4.4 mils x 4.4 mils

Metallization Mask Layout



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